

P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | |
|---------------------|------------------------------------|--------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) | | | |
| - 30 | 0.012 at V _{GS} = - 10 V | - 11.4 | | | |
| - 30 | 0.019 at V _{GS} = - 4.5 V | - 9.1 | | | |

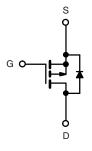
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Advanced High Cell Density Process
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- · Load Switches
 - Notebook PCs
 - Desktop PCs



P-Channel MOSFET

| | SO-8 | | |
|--------------------------|----------|------------------|-------------|
| S 1 S 2 S 3 G 4 | | 8 7 6 5 | D D D |
| | Top View | - | |

Ordering Information: Si4425BDY-T1-E3 (Lead (Pb)-free)

Si4425BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS | T _A = 25 °C, unle | ss otherwise r | noted | | |
|---|------------------------------|-----------------------------------|-------------|--------------|------|
| Parameter | | Symbol | 10 s | Steady State | Unit |
| Drain-Source Voltage | | V _{DS} | - 30 | | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | | |
| Continuous Dunin Courset /T 150 °C\d | T _A = 25 °C | - I _D | - 11.4 | - 8.8 | ^ |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 70 °C | | - 9.1 | - 7.0 | |
| Pulsed Drain Current | | I _{DM} | - 50 | | Α |
| Continuous Source Current (Diode Conduction) ^a | | I _S | - 2.1 | - 1.3 | |
| Mariana Barra Biratina | T _A = 25 °C | P _D | 2.5 1.5 | | W |
| Maximum Power Dissipation ^a | T _A = 70 °C |] 'D | 1.6 | 0.9 | VV |
| Operating Junction and Storage Temperature Range | | T _J , T _{sta} | - 55 to 150 | | °C |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Manipulation to Application | t ≤ 10 s | R _{thJA} | 40 | 50 | | |
| Maximum Junction-to-Ambient ^a | Steady State | ' 'thJA | 70 | 85 | °C/W | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 15 | 18 | 1 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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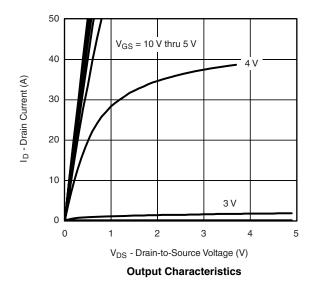
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | |
|--|---------------------|---|-------|-------|-------|------|--|
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | - 1.0 | | - 3.0 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| Zava Cata Valtaga Dvain Current | | V _{DS} = - 30 V, V _{GS} = 0 V | | | - 1 | μΑ | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | | | - 5 | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$ | - 50 | | | Α | |
| | R _{DS(on)} | V _{GS} = - 10 V, I _D = - 11.4 A | | 0.010 | 0.012 | Ω | |
| Drain-Source On-State Resistance ^a | | V _{GS} = - 4.5 V, I _D = - 9.1 A | | 0.015 | 0.019 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 15 V, I _D = - 11.4 A | | 29 | | S | |
| Diode Forward Voltage ^a | V_{SD} | I _S = - 2.5 A, V _{GS} = 0 V | | - 0.8 | - 1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Q_g | | | 64 | 100 | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -11.4 \text{ A}$ | | 11 | | nC | |
| Gate-Drain Charge | Q _{gd} | | | 17 | | 1 | |
| Turn-On Delay Time | t _{d(on)} | | | 15 | 25 | | |
| Rise Time | t _r | V_{DD} = - 15 V, R_L = 15 Ω | | 13 | 20 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_g=6~\Omega$ | | 100 | 150 | ns | |
| Fall Time | t _f | | | 53 | 80 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = - 2.5 A, dI/dt = 100 A/μs | | 41 | 80 | | |

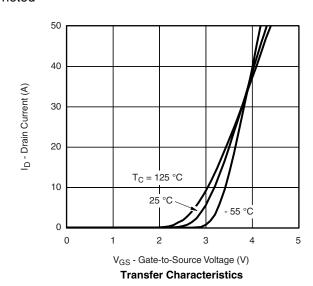
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

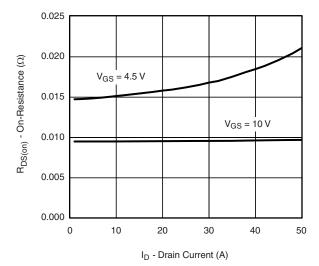
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



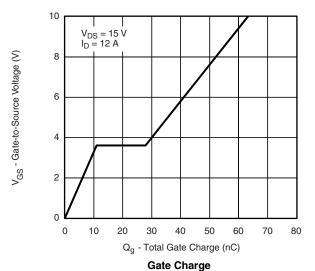


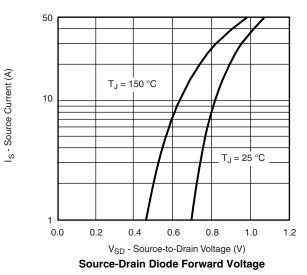


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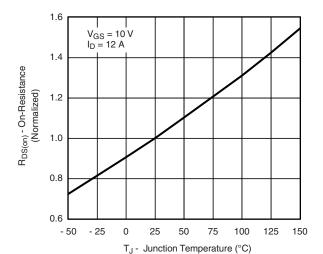
On-Resistance vs. Drain Current



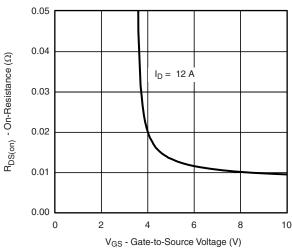


5000 4000 Ciss 3000 2000 1000 Crss 0 6 12 18 24 30

 V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature

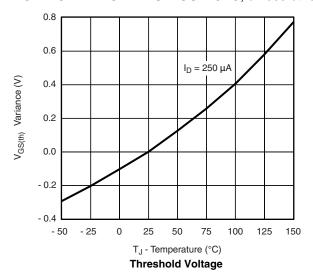


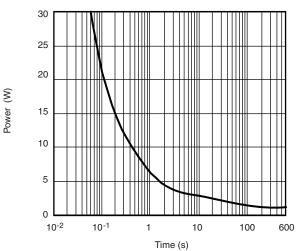
On-Resistance vs. Gate-to-Source Voltage

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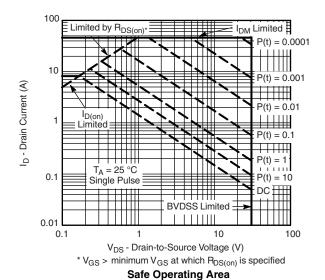
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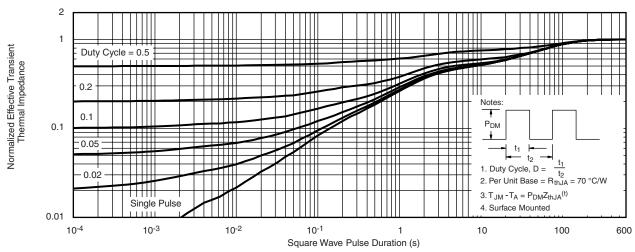
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Power, Junction-to-Ambient

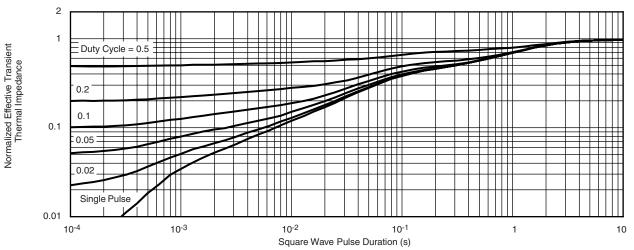




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



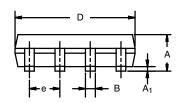
Normalized Thermal Transient Impedance, Junction-to-Foot

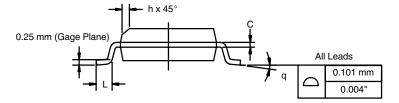
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







| | MILLIM | IETERS | INCHES | | | |
|--------------------------------|--------|--------|-----------|-------|--|--|
| DIM | Min | Max | Min | Max | | |
| Α | 1.35 | 1.75 | 0.053 | 0.069 | | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | | |
| В | 0.35 | 0.51 | 0.014 | 0.020 | | |
| С | 0.19 | 0.25 | 0.0075 | 0.010 | | |
| D | 4.80 | 5.00 | 0.189 | 0.196 | | |
| Е | 3.80 | 4.00 | 0.150 | 0.157 | | |
| е | 1.27 | BSC | 0.050 BSC | | | |
| Н | 5.80 | 6.20 | 0.228 | 0.244 | | |
| h | 0.25 | 0.50 | 0.010 | 0.020 | | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | | |
| q | 0° | 8° | 0° | 8° | | |
| S | 0.44 | 0.64 | 0.018 | 0.026 | | |
| ECN: C-06527-Rev. I. 11-Sep-06 | | | | | | |

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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